



SCT3080KLGC11 Information



For Reference Only

Part Number SCT3080KLGC11

Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET NCH 1.2KV 31A TO247N

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SCT3080KLGC11 Specifications

Manufacturer Part Number SCT3080KLGC11 Manufacturer Rohm Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, 4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Manufacturer Part Number	SCT3080KLGC11
Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Manufacturer	Rohm Semiconductor
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Series-FET TypeN-ChannelTechnologySiCFET (Silicon Carbide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)18VVgs(th) (Max) @ Id5.6V @ 5mAGate Charge (Qg) (Max) @ Vgs60nC @ 18VInput Capacitance (Ciss) (Max) @ Vds785pF @ 800VVgs (Max)+22V, -4VFET Feature-Power Dissipation (Max)165W (Tc)Rds On (Max) @ Id, Vgs104 mOhm @ 10A, 18VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247NPackage / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package 70-247N Package / Case 71-20-20-20-20-20-20-20-20-20-20-20-20-20-	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature Mounting Type Through Hole Supplier Device Package TO-247N Package / Case	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature Mounting Type Through Hole Supplier Device Package TO-247N Package / Case 31A (Tc) 18V 5.6V @ 5mA 60nC @ 18V 785pF @ 800V 422V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) 175°C (TJ) Through Hole	Technology	SiCFET (Silicon Carbide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.6V @ 5mA Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 60nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	31A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	18V
Input Capacitance (Ciss) (Max) @ Vds 785pF @ 800V Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Vgs(th) (Max) @ Id	5.6V @ 5mA
Vgs (Max) +22V, -4V FET Feature - Power Dissipation (Max) 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Gate Charge (Qg) (Max) @ Vgs	60nC @ 18V
FET Feature - 165W (Tc) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	785pF @ 800V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Vgs (Max)	+22V, -4V
Rds On (Max) @ Id, Vgs 104 mOhm @ 10A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	FET Feature	-
Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Power Dissipation (Max)	165W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247N Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	104 mOhm @ 10A, 18V
Supplier Device Package TO-247N Package / Case TO-247-3	Operating Temperature	175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247N
Report errors?	Package / Case	TO-247-3
		Report errors?

SCT3080KLGC11 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SCT3080KLGC11 Payment Methods



















SCT3080KLGC11 Shipping Methods













If you have any question about SCT3080KLGC11, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com